

ABSTRACT

This invention relates to a plasma processing system. A common problem in the manufacture of semiconductors is the maintenance of a constant fluid flow throughout the chamber in which the semiconductors are being etched. The focus ring described herein helps control fluid flow such that all (or substantially all) of a substrate (e.g., semiconductor) surface is exposed to a constant flow of plasma throughout the etching process. An even fluid flow is maintained by adjusting the configuration of a focus ring, a pumping baffle, or a focus ring working with an auxiliary focus ring with respect to the semiconductor surface. By manipulating the position of the focus ring, pumping baffle, and auxiliary focus ring, fluid flow over the surface of the semiconductor can be increased, decreased, or kept stagnant.